

In re of: SAIJO=

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one of claims 1 or 2 wherein the interposer-forming clad plate for use in the semiconductor device is formed by previously applying an activating treatment to the bonded surfaces of the copper foil and the nickel foil or nickel plating in a vacuum vessel and then laminating the copper foil and the nickel foil material or nickel plating and cold press-bonding them at a rolling reduction of 0.1 to 3% in which the activating treatment is applied <1> in an inert gas atmosphere at an extremely low pressure of  $1 \times 10^1$  to  $1 \times 10^{-2}$  Pa, <2> using the nickel plated copper foil material and the copper foil material as one electrode A having the bonding surfaces grounded to the earth, respectively, and conducting glow discharge by applying an AC current at 1 to 50 MHz between it and the other electrode B supported insulatively and <4> applying sputter etching, <3> with the area of the electrode exposed in plasmas caused by the glow discharge being 1/3 or less of the electrode B.

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Please add claims 7 and 8 as follows:

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7 (New).-- A method of manufacturing an interposer-forming clad layer for use in a semiconductor device as defined in claim 3 wherein the interposer-forming clad plate for use in the semiconductor device is formed by previously applying an activating treatment to the bonded surfaces of the copper foil and the nickel foil or nickel plating in a vacuum vessel and then laminating the copper foil and the nickel foil material or nickel plating and cold press-bonding them at a rolling reduction of 0.1 to 3% in which the activating treatment is applied <1> in an inert gas atmosphere at an extremely low pressure of  $1 \times 10^1$  to  $1 \times 10^{-2}$  Pa, <2> using the nickel plated copper foil material and the copper foil material as one electrode A having the bonding surfaces grounded to the earth,

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respectively, and conducting glow discharge by applying an AC current at 1 to 50 MHz between it and the other electrode B supported insulatively and <4> applying sputter etching, <3> with the area of the electrode exposed in plasmas caused by the glow discharge being 1/3 or less of the electrode B.--

8 (New).-- An interposer for use in a semiconductor device in which a clad plate as defined in claim 3 is etched selectively to form connecting bumps with a semiconductor chip and a wiring layer, the semiconductor chip and the wiring layer are connected by way of the semiconductor chip connection bumps using anisotropically conductive adhesives and conduction of the interposer in the direction of the thickness is taken by way of a columnar conductor formed by etching.--

If, inadvertently, a proper multiple dependent claim has not been amended to reduce it to single dependency, please amend it to be dependent solely on the first-mentioned claim, or, if that is not possible, please cancel the claim and notify the undersigned.

#### REMARKS

The above amendments to the claims are being made in order to eliminate multiple dependency and for the purpose of reducing the filing fee. Please enter this amendment prior to calculation of the filing fee in this case.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "Version with Markings to Show Changes Made."